





200V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C
200V	750mΩ @ Vgs = 10V	2.3A
	$780\text{m}\Omega$ @ Vgs = 5V	2.3A

Description and Applications

This MOSFET features low on-resistance, fast switching and a high avalanche withstand capability, making it ideal for high efficiency power management applications.

- · SLIC line drivers for VoIP applications
- · Transformer driving switch
- · Power management functions
- Motor control
- Uninterrupted power supply

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) test in production
- High avalanche energy pulse withstand capability
- Low gate drive voltage (Logic level capable)
- Low input capacitance
- · Low on-resistance
- · Fast switching speed
- "Green" Component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

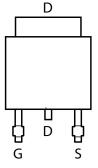
Mechanical Data

- Case: TO252-3L
- Case Material: Molded Plastic "Green" Molding Compound, UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)

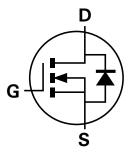




Top View



Pin Out - Top View



Equivalent Circuit

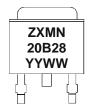
Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
ZXMN20B28KTC	See below	13	16	2,500	

Note:

1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information



ZXMN = Product Type Marking Code, Line 1 20B28 = Product Type Marking Code, Line 2 YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01-52)





Maximum Ratings @T_A = 25°C unless otherwise specified

C	haracteristic		Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	200	V
Gate-Source voltage			V _{GS}	±20	V
Single Pulsed Avalanche Ene	ergy	(Note 7)	E _{AS}	73	mJ
Single Pulsed Avalanche Cui	rrent	(Note 7)	I _{AS}	5.5	A
Repetitive Avalanche Energy		(Note 4)	lote 4) E _{AR}		mJ
Repetitive Avalanche Current (Note 4)		(Note 4)	I _{AR}	5.5	А
Continuous Drain current	V _{GS} = 10V	(Note 3) T _A = 70°C (Note 3) (Note 2)	ID	2.3 1.8 1.5	А
Pulsed Drain current V _{GS} = 10V		(Note 4)	I _{DM}	17.3	Α
Continuous Source current (Body diode)		(Note 2)	I _S	5.7	Α
Pulsed Source current (Body diode)		(Note 4)	I _{SM}	17.3	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
	(Note 2)		4.3 34.4	
Power dissipation Linear derating factor	(Note 3)	P _D	10.2 76.0	W mW/°C
	(Note 6)		2.2 17.4	
	(Note 2)		29.1	
Thermal Resistance, Junction to Ambient	(Note 3)	$R_{ heta JA}$	12.3	°C/W
	(Note 6)	Ť	57.3	
Thermal Resistance, Junction to Lead	(Note 5)	$R_{ heta JL}$	1.15	°C/W
Operating and storage temperature range		TJ, T _{STG}	-55 to 150	°C

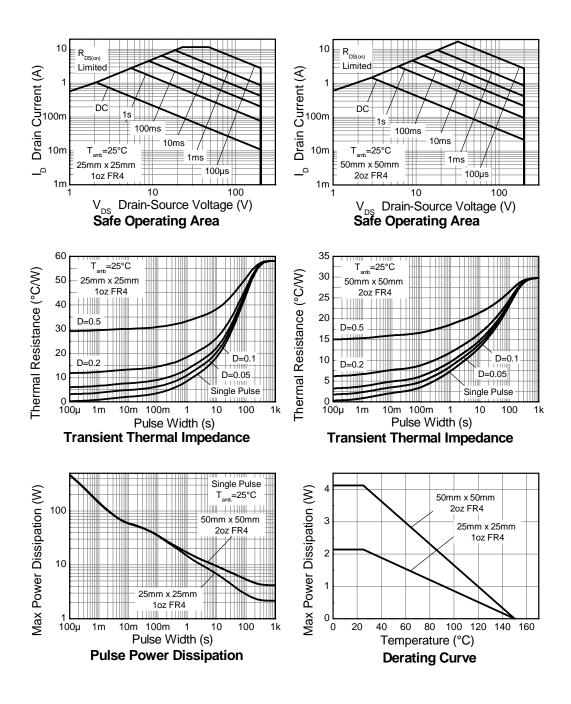
Notes:

- 2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 3. Same as note 2, except the device is measured at $t \le 10$ sec.
- 4. Same as note 2, except the device is operating in a repetitive state with pulse width and duty cycle limited by maximum junction temperature.
- 5. Thermal resistance from junction to solder-point (at the end of the drain lead).
- 6. For a device surface mounted on 25mm x 1.6mm FR4 PCB with the high coverage single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. UIS in production with L = 4.83mH, IAS = 5.5A, RG = 25 Ω , V_{DD} = 100V, starting TJ = 25 $^{\circ}$ C.





Thermal Characteristics







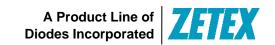
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	200		_	V	$I_D = 250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current	I _{DSS}	_		500	nA	V _{DS} = 200V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	1	1.6	2.5	V	$I_D=250\mu A,V_{DS}=V_{GS}$
Static Drain Source On Registence (Note 9)	Ь		0.650	0.750	Ω	$V_{GS} = 10V, I_D = 2.75A$
Static Drain-Source On-Resistance (Note 8)	R _{DS} (ON)		0.670	0.780		$V_{GS} = 5V, I_D = 2.75A$
Forward Transconductance (Notes 8 & 9)	g _{fs}	_	6.13		S	$V_{DS} = 30V, I_D = 2.75A$
Diode Forward Voltage (Note 8)	V_{SD}	_	0.860	0.950	٧	$I_S = 5.5A, V_{GS} = 0V$
Reverse recovery time (Note 9)	t _{rr}	_	177	_	ns	$I_S = 6.5A, V_{GS} = 0V,$
Reverse recovery charge (Note 9)	Q _{rr}	_	1.4	_	μС	di/dt = 100A/μs
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	358		pF	V 05V V 0V
Output Capacitance	Coss	_	50		pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1MHz
Reverse Transfer Capacitance	Crss	_	6.1	_	pF	1 - 1101112
Total Gate Charge	Q_g	_	8.1	_	nC	V 400V V 5V
Gate-Source Charge	Q_{gs}	_	1.4	_	nC	$V_{DS} = 120V, V_{GS} = 5V$ In = 6.5A
Gate-Drain Charge	Q_{gd}	_	3.9	_	nC	1D = 0.5A
Turn-On Delay Time (Note 10)	t _{D(on)}	_	17.8		ns	
Turn-On Rise Time (Note 10)	t _r	_	76.9		ns	V _{DD} = 100V, V _{GS} = 5V
Turn-Off Delay Time (Note 10)	t _{D(off)}	_	44.7		ns	$I_D = 6.5A, R_G \cong 25\Omega$
Turn-Off Fall Time (Note 10)	t _f		57.1		ns	

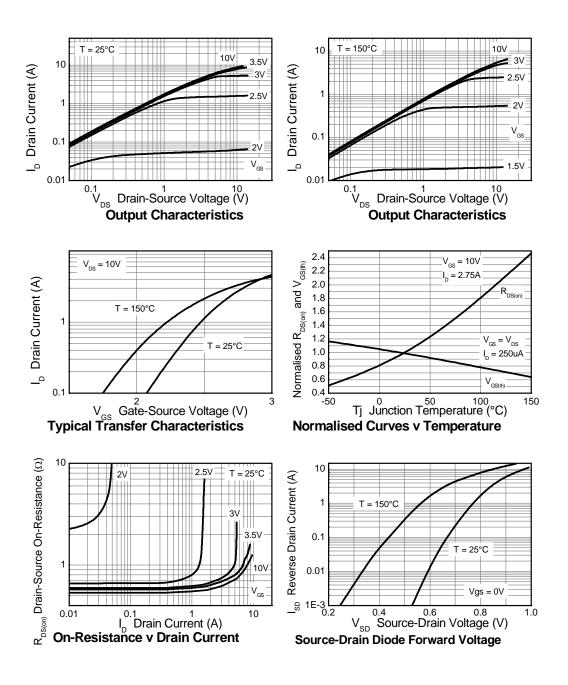
Notes:

- 8. Measured under pulsed conditions. Pulse width $\le 300\mu s$; duty cycle $\le 2\%$ 9. For design aid only, not subject to production testing. 10. Switching characteristics are independent of operating junction temperatures.



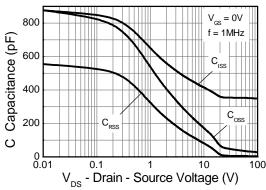


Typical Characteristics

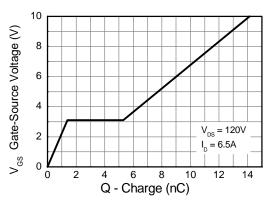




Typical Characteristics - continued

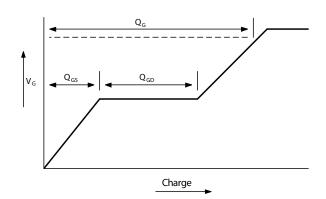




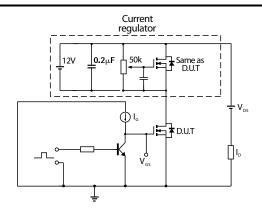


Gate-Source Voltage v Gate Charge

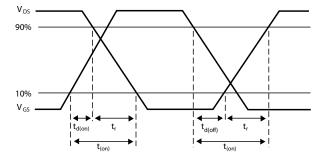
Test Circuits



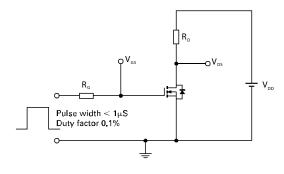
Basic gate charge waveform



Gate charge test circuit

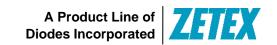


Switching time waveforms

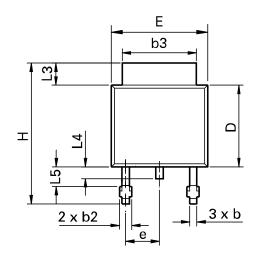


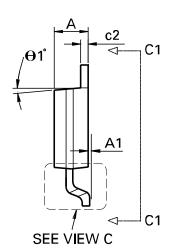
Switching time test circuit

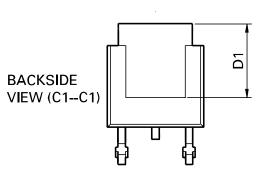


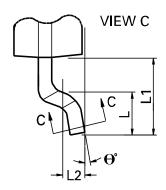


Package Outline Dimensions







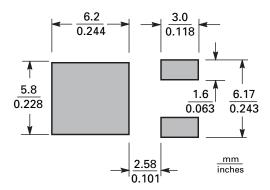


DIM	DIM Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	Н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
С	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	_





Suggested Pad Layout



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